Silicon Switching Diode

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Continuous Reverse Voltage	V_R	100	V
Recurrent Peak Forward Current	I _F	200	mA
Peak Forward Surge Current Pulse Width = 10 μs	I _{FM(surge)}	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T _A = 25°C Derated above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	555	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T _A = 25°C Derated above 25°C	P _D	360 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	345	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 × 1.0 Inch Pad



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MARKING DIAGRAM



CASE 463 SOT-416 STYLE 2



XX = Specific Device Code

M = Date Code

Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS16TT1G	SOT-416 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Forward Voltage (I _F = 1.0 mA) (I _F = 10 mA) (I _F = 50 mA) (I _F = 150 mA)	V _F	- - - -	715 866 1000 1250	mV
Reverse Current $(V_R = 100 \text{ V})$ $(V_R = 75 \text{ V}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ V}, T_J = 150^{\circ}\text{C})$	I _R	- - -	1.0 50 30	μΑ
Capacitance (V _R = 0, f = 1.0 MHz)	C _D	-	2.0	pF
Reverse Recovery Time (I _F = I _R = 10 mA, R _L = 50 Ω) (Figure 1)	t _{rr}	-	6.0	ns
Stored Charge (I _F = 10 mA to V_R = 6.0 V, R_L = 500 Ω) (Figure 2)	QS	-	45	PC
Forward Recovery Voltage ($I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$) (Figure 3)	V _{FR}	-	1.75	V

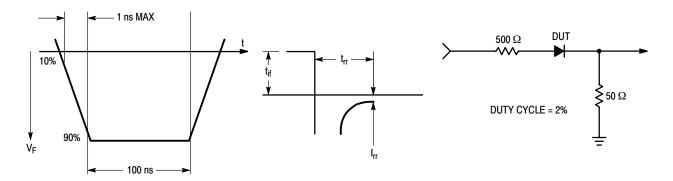


Figure 1. Reverse Recovery Time Equivalent Test Circuit

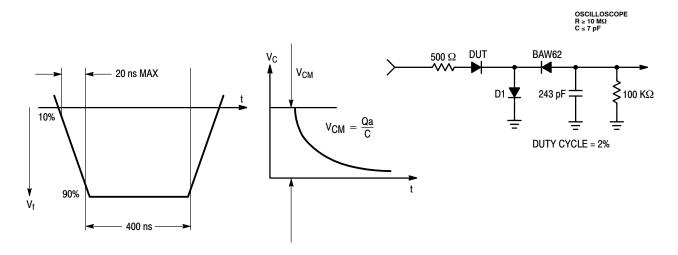


Figure 2. Stored Charge Equivalent Test Circuit

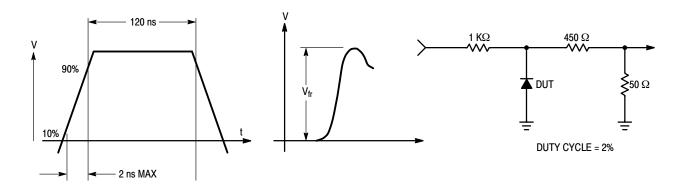
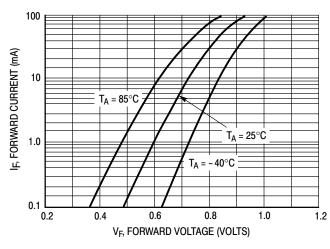


Figure 3. Forward Recovery Voltage Equivalent Test Circuit



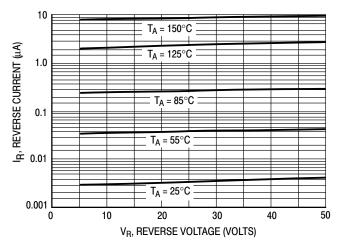


Figure 4. Forward Voltage

Figure 5. Leakage Current

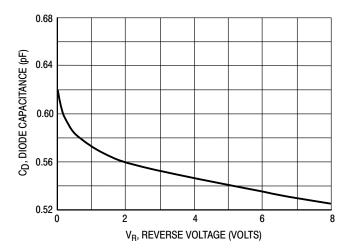


Figure 6. Capacitance

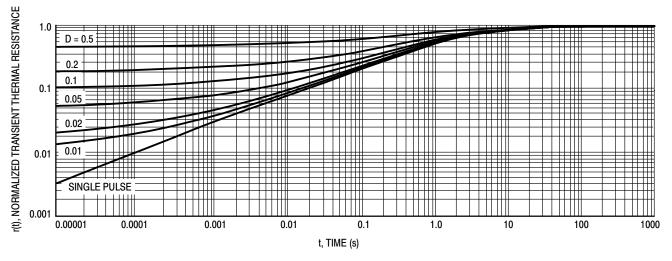


Figure 7. Normalized Thermal Response

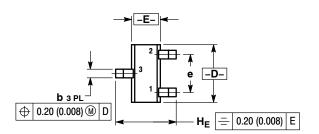
MECHANICAL CASE OUTLINE

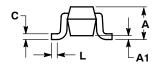




SC-75/SOT-416 CASE 463-01 ISSUE G

DATE 07 AUG 2015





STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

-		MILLIMETERS			INCHES		
L	DIM	MIN	NOM	MAX	MIN	NOM	MAX
	Α	0.70	0.80	0.90	0.027	0.031	0.035
L	A1	0.00	0.05	0.10	0.000	0.002	0.004
	b	0.15	0.20	0.30	0.006	0.008	0.012
	С	0.10	0.15	0.25	0.004	0.006	0.010
	D	1.55	1.60	1.65	0.061	0.063	0.065
	Е	0.70	0.80	0.90	0.027	0.031	0.035
	е	1.00 BSC			0.04 BSC)	
	L	0.10	0.15	0.20	0.004	0.006	0.008
	HE	1.50	1.60	1.70	0.060	0.063	0.067

GENERIC MARKING DIAGRAM*

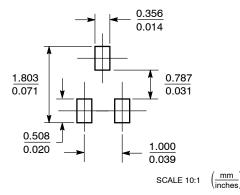


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SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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